

## MOSFET

Metal Oxide Semiconductor Field Effect Transistor

### OptiMOS™

OptiMOS™ 5 Power-Transistor, 80 V  
BSZ110N08NS5

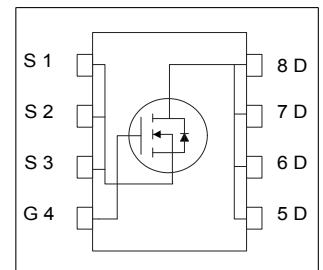
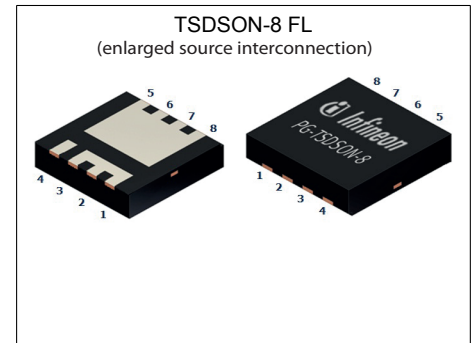
## Data Sheet

Rev. 2.1  
Final

## 1 Description

### Features

- Ideal for high frequency switching and sync. rec.
- Optimized technology for DC/DC converters
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Very low on-resistance  $R_{DS(on)}$
- N-channel, normal level
- 100% avalanche tested
- Pb-free plating; RoHS compliant
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Halogen-free according to IEC61249-2-21
- Higher solder joint reliability with enlarged source interconnection



**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DS}$	80	V
$R_{DS(on),max}$	11.0	m $\Omega$
$I_D$	40	A
$Q_{oss}$	19	nC
$Q_G(0V..10V)$	15	nC

Type / Ordering Code	Package	Marking	Related Links
BSZ110N08NS5	PG-TSDSON-8 FL	110N08N	-

<sup>1)</sup> J-STD20 and JESD22

**Table of Contents**

Description .....	2
Maximum ratings .....	4
Thermal characteristics .....	4
Electrical characteristics .....	5
Electrical characteristics diagrams .....	7
Package Outlines .....	11
Revision History .....	12
Disclaimer .....	12

## 2 Maximum ratings

at  $T_j = 25\text{ °C}$ , unless otherwise specified

**Table 2 Maximum ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	$I_D$	-	-	40 33	A	$T_C=25\text{ °C}$ $T_C=100\text{ °C}$
Pulsed drain current <sup>1)</sup>	$I_{D,pulse}$	-	-	160	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse <sup>2)</sup>	$E_{AS}$	-	-	40	mJ	$I_D=20\text{ A}$ , $R_{GS}=25\text{ }\Omega$
Gate source voltage	$V_{GS}$	-20	-	20	V	-
Power dissipation	$P_{tot}$	-	-	50	W	$T_C=25\text{ °C}$
Operating and storage temperature	$T_j, T_{stg}$	-55	-	150	°C	IEC climatic category; DIN IEC 68-1: 55/150/56

## 3 Thermal characteristics

**Table 3 Thermal characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{thJC}$	-	1.5	2.5	K/W	-
Device on PCB, 6 cm <sup>2</sup> cooling area <sup>3)</sup>	$R_{thJA}$	-	-	60	K/W	-

<sup>1)</sup> See figure 3 for more detailed information

<sup>2)</sup> See figure 13 for more detailed information

<sup>3)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

## 4 Electrical characteristics

**Table 4 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	80	-	-	V	$V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2.2	3	3.8	V	$V_{DS}=V_{GS}$ , $I_D=22\text{ }\mu\text{A}$
Zero gate voltage drain current	$I_{DSS}$	-	0.1 10	1 100	$\mu\text{A}$	$V_{DS}=80\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ }^\circ\text{C}$ $V_{DS}=80\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=125\text{ }^\circ\text{C}$
Gate-source leakage current	$I_{GSS}$	-	1	100	nA	$V_{GS}=20\text{ V}$ , $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	9.6 13.4	11.0 16.3	m $\Omega$	$V_{GS}=10\text{ V}$ , $I_D=20\text{ A}$ $V_{GS}=6\text{ V}$ , $I_D=5\text{ A}$
Gate resistance	$R_G$	-	1.4	2	$\Omega$	-
Transconductance	$g_{fs}$	17	33	-	S	$ V_{DS} >2 I_D R_{DS(on)max}$ , $I_D=20\text{ A}$

**Table 5 Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	$C_{iss}$	-	1000	1300	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=40\text{ V}$ , $f=1\text{ MHz}$
Output capacitance <sup>1)</sup>	$C_{oss}$	-	180	235	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=40\text{ V}$ , $f=1\text{ MHz}$
Reverse transfer capacitance <sup>1)</sup>	$C_{rss}$	-	11	19	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=40\text{ V}$ , $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	9	-	ns	$V_{DD}=40\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=20\text{ A}$ , $R_{G,ext}=1.6\text{ }\Omega$
Rise time	$t_r$	-	3	-	ns	$V_{DD}=40\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=20\text{ A}$ , $R_{G,ext}=1.6\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	15	-	ns	$V_{DD}=40\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=20\text{ A}$ , $R_{G,ext}=1.6\text{ }\Omega$
Fall time	$t_f$	-	3	-	ns	$V_{DD}=40\text{ V}$ , $V_{GS}=10\text{ V}$ , $I_D=20\text{ A}$ , $R_{G,ext}=1.6\text{ }\Omega$

**Table 6 Gate charge characteristics<sup>2)</sup>**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	$Q_{gs}$	-	4.9	-	nC	$V_{DD}=40\text{ V}$ , $I_D=20\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge <sup>1)</sup>	$Q_{gd}$	-	3.3	5	nC	$V_{DD}=40\text{ V}$ , $I_D=20\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	$Q_{sw}$	-	5.4	-	nC	$V_{DD}=40\text{ V}$ , $I_D=20\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total	$Q_g$	-	15	18.5	nC	$V_{DD}=40\text{ V}$ , $I_D=20\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	4.9	-	V	$V_{DD}=40\text{ V}$ , $I_D=20\text{ A}$ , $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total, sync. FET	$Q_{g(sync)}$	-	13	-	nC	$V_{DS}=0.1\text{ V}$ , $V_{GS}=0\text{ to }10\text{ V}$
Output charge <sup>1)</sup>	$Q_{oss}$	-	19	26	nC	$V_{DD}=40\text{ V}$ , $V_{GS}=0\text{ V}$

<sup>1)</sup> Defined by design. Not subject to production test

<sup>2)</sup> See "Gate charge waveforms" for parameter definition

**Table 7 Reverse diode**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	$I_S$	-	-	40	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	160	A	$T_C=25\text{ °C}$
Diode forward voltage	$V_{SD}$	-	0.88	1.2	V	$V_{GS}=0\text{ V}, I_F=20\text{ A}, T_J=25\text{ °C}$
Reverse recovery time <sup>1)</sup>	$t_{rr}$	-	36	72	ns	$V_R=40\text{ V}, I_F=20\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge <sup>1)</sup>	$Q_{rr}$	-	36	72	nC	$V_R=40\text{ V}, I_F=20\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$

<sup>1)</sup> Defined by design. Not subject to production test

## 5 Electrical characteristics diagrams

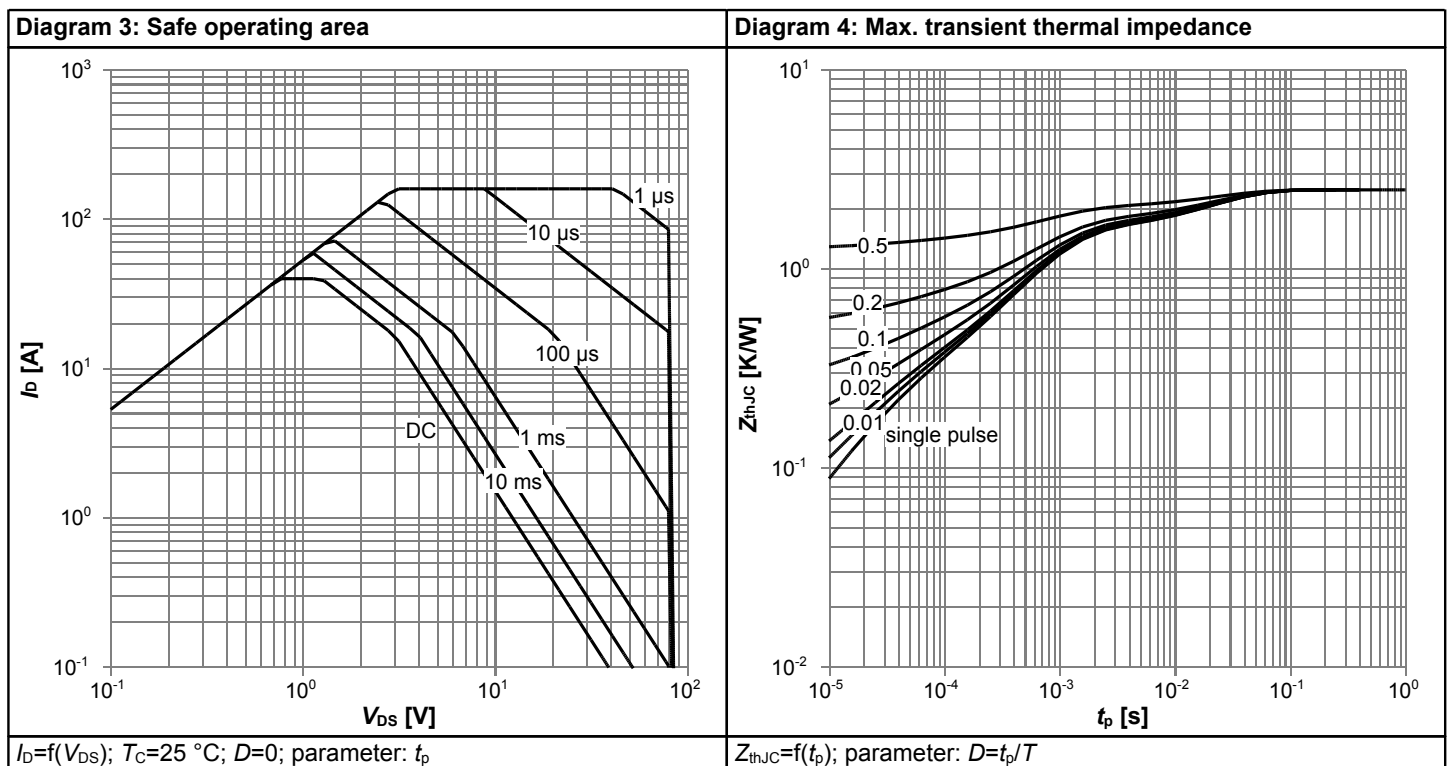
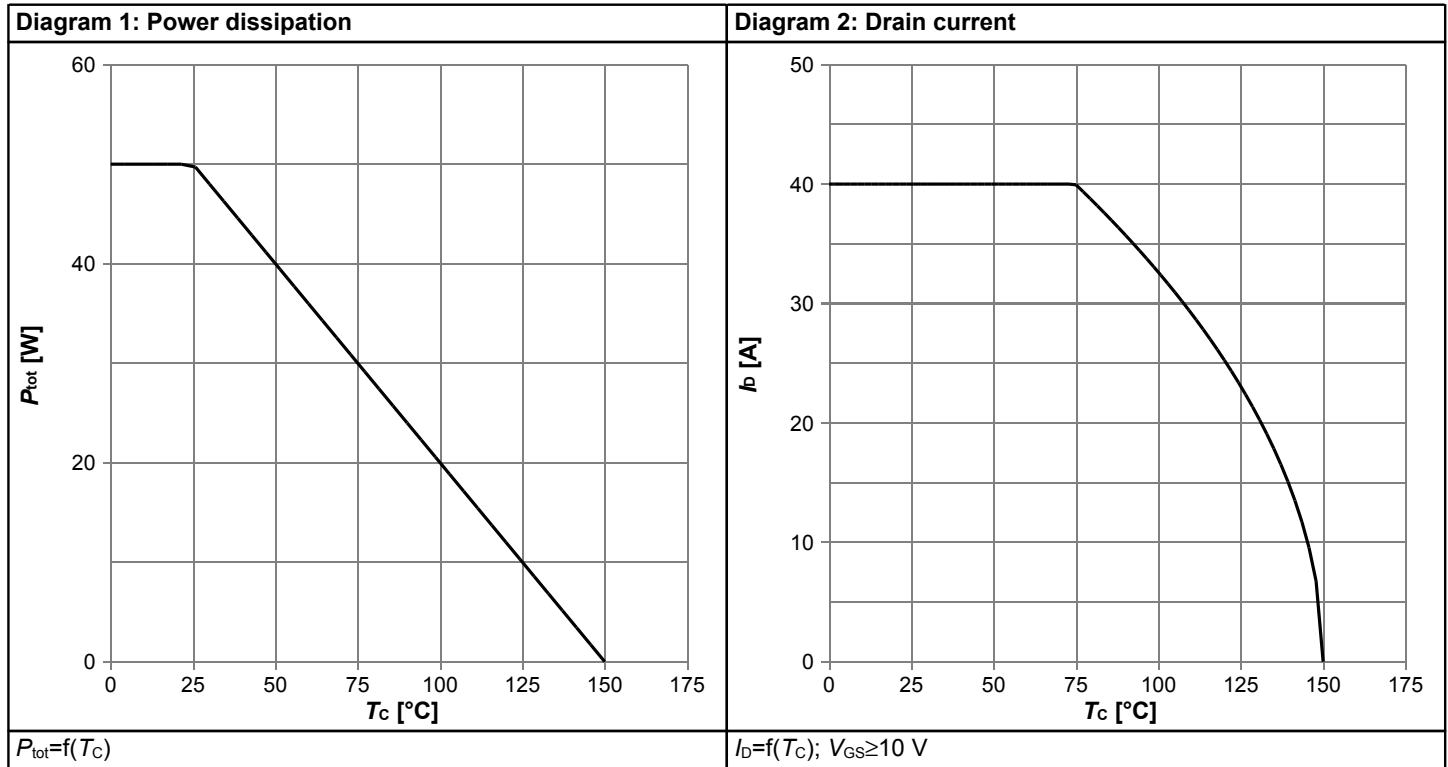
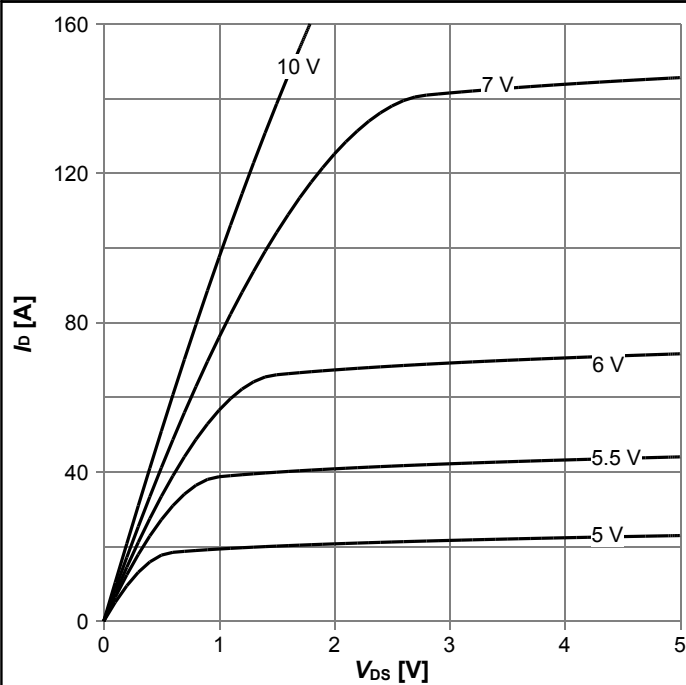
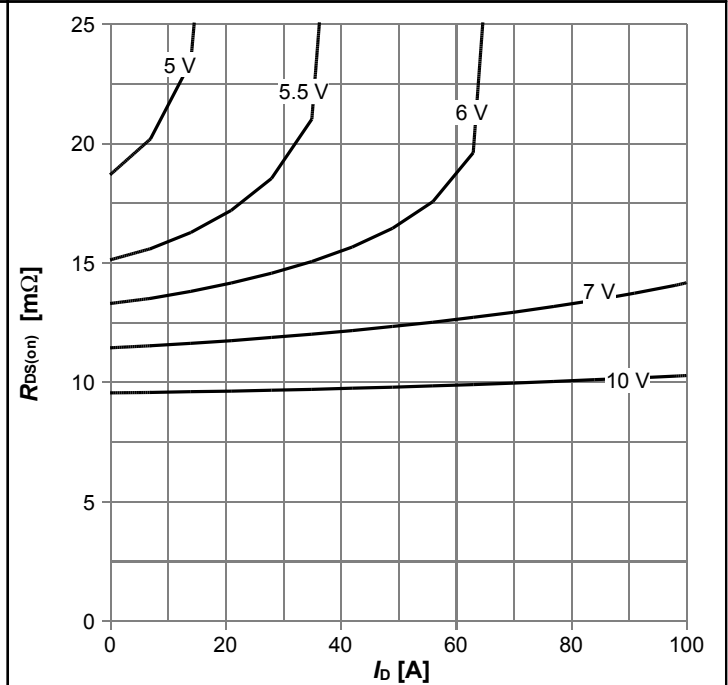


Diagram 5: Typ. output characteristics



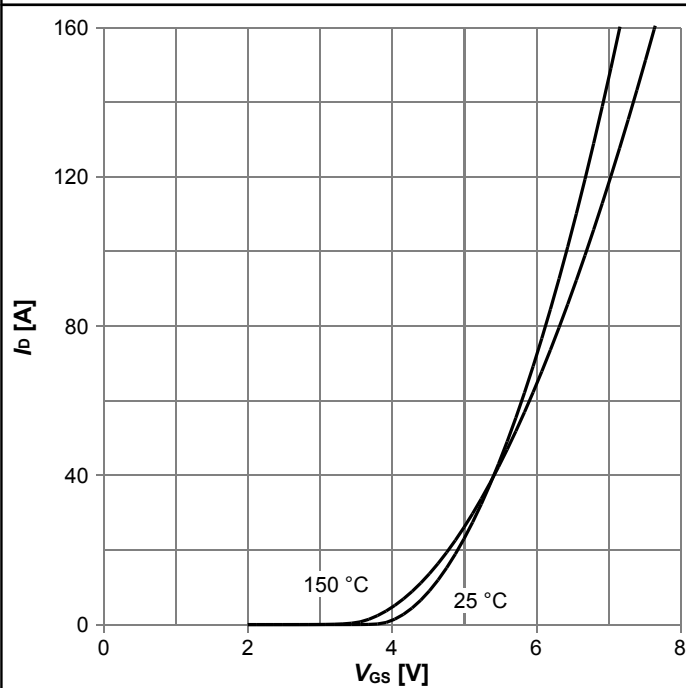
$I_D=f(V_{DS})$ ;  $T_j=25\text{ }^\circ\text{C}$ ; parameter:  $V_{GS}$

Diagram 6: Typ. drain-source on resistance



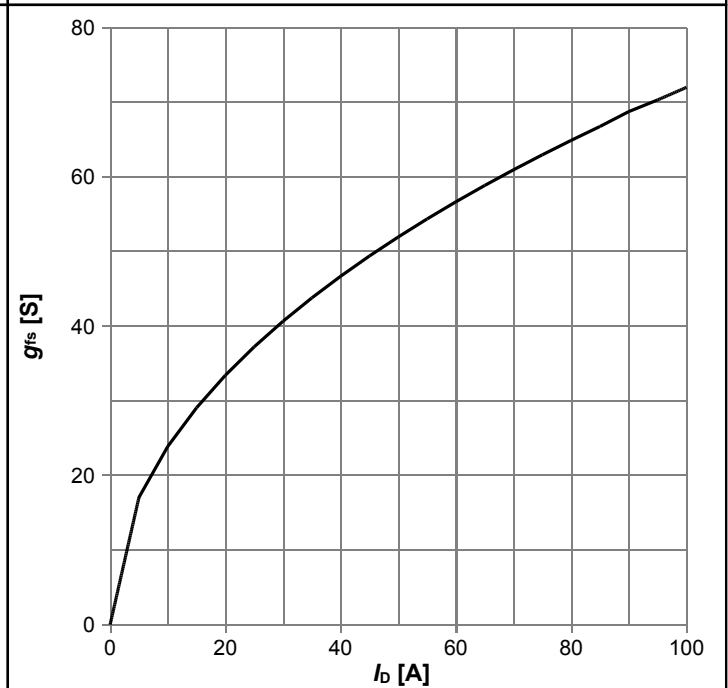
$R_{DS(on)}=f(I_D)$ ;  $T_j=25\text{ }^\circ\text{C}$ ; parameter:  $V_{GS}$

Diagram 7: Typ. transfer characteristics



$I_D=f(V_{GS})$ ;  $|V_{DS}|>2|I_D|R_{DS(on)max}$ ; parameter:  $T_j$

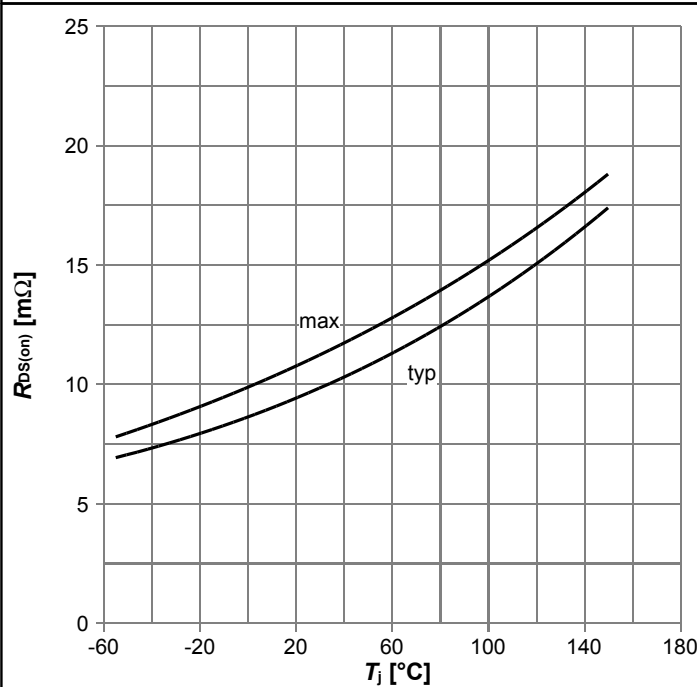
Diagram 8: Typ. forward transconductance



$g_{fs}=f(I_D)$ ;  $T_j=25\text{ }^\circ\text{C}$

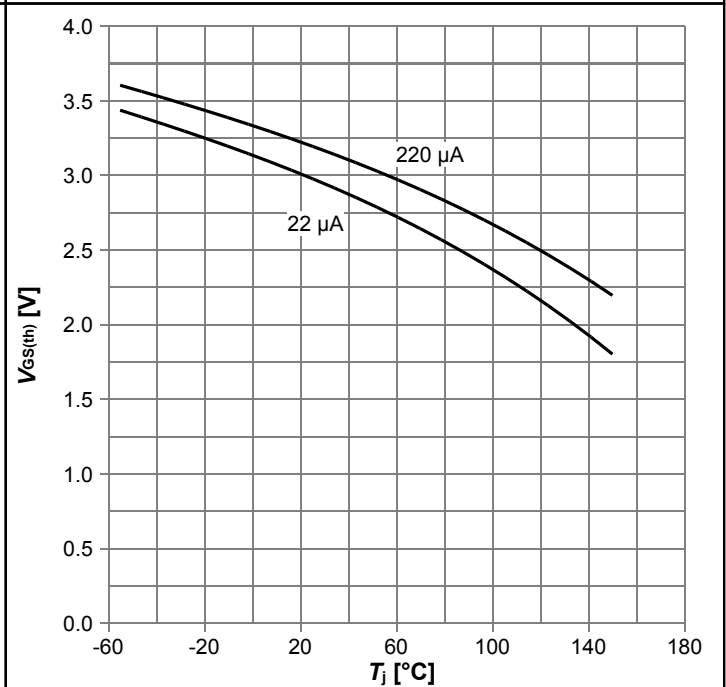


Diagram 9: Drain-source on-state resistance



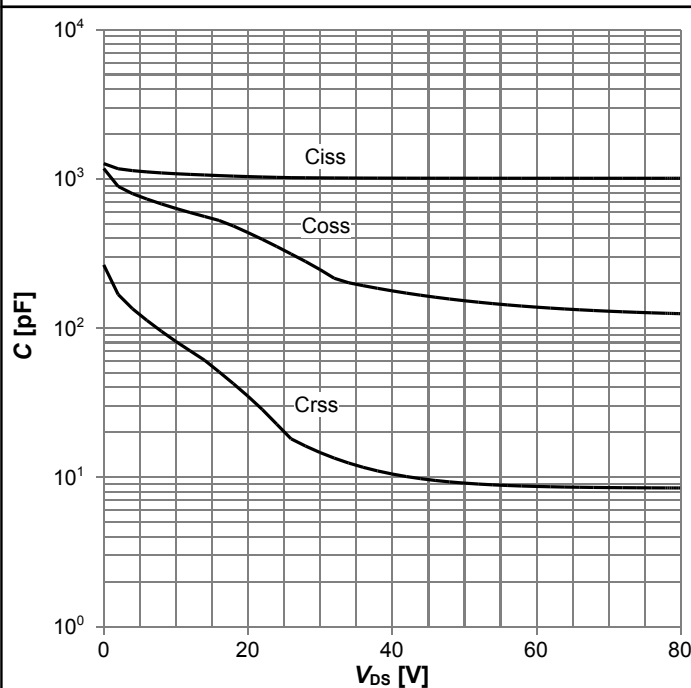
$R_{DS(on)}=f(T_j); I_D=20\text{ A}; V_{GS}=10\text{ V}$

Diagram 10: Typ. gate threshold voltage



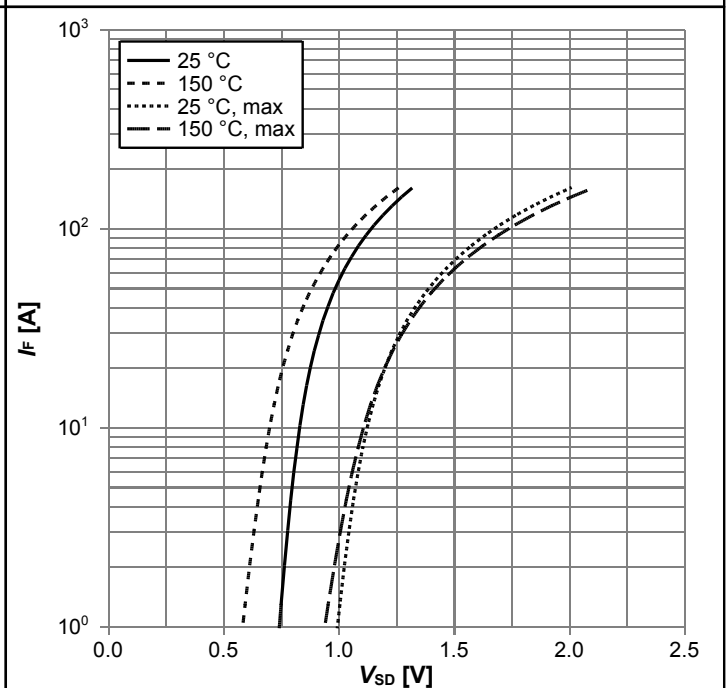
$V_{GS(th)}=f(T_j); V_{GS}=V_{DS}; \text{parameter: } I_D$

Diagram 11: Typ. capacitances



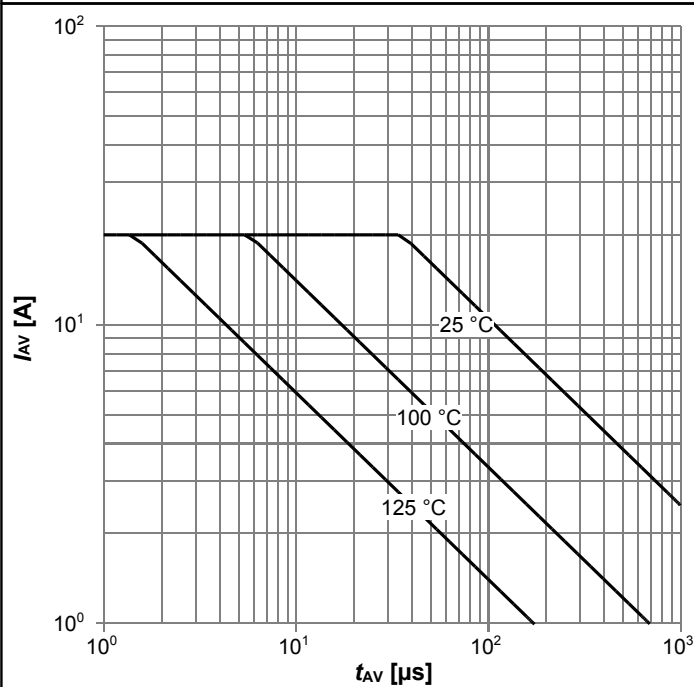
$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$

Diagram 12: Forward characteristics of reverse diode



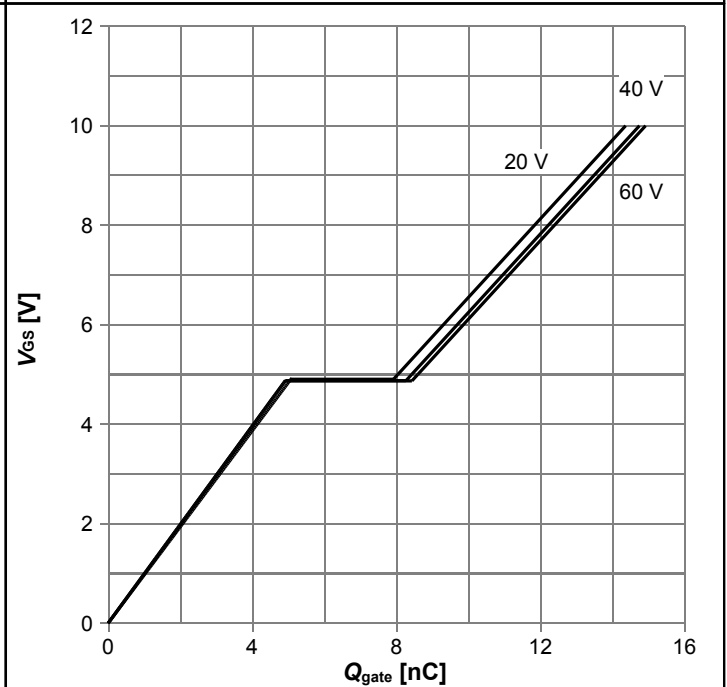
$I_F=f(V_{SD}); \text{parameter: } T_j$

Diagram 13: Avalanche characteristics



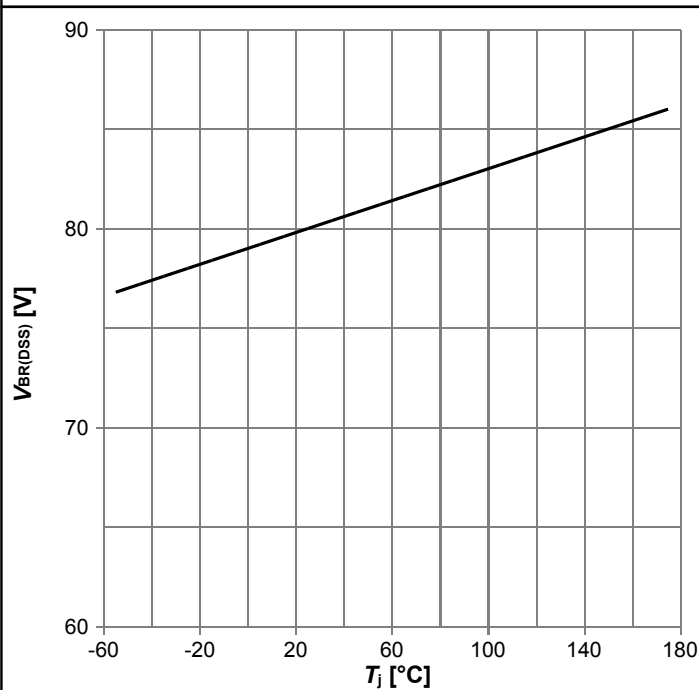
$I_{AS}=f(t_{AV}); R_{GS}=25 \Omega$ ; parameter:  $T_{j(start)}$

Diagram 14: Typ. gate charge



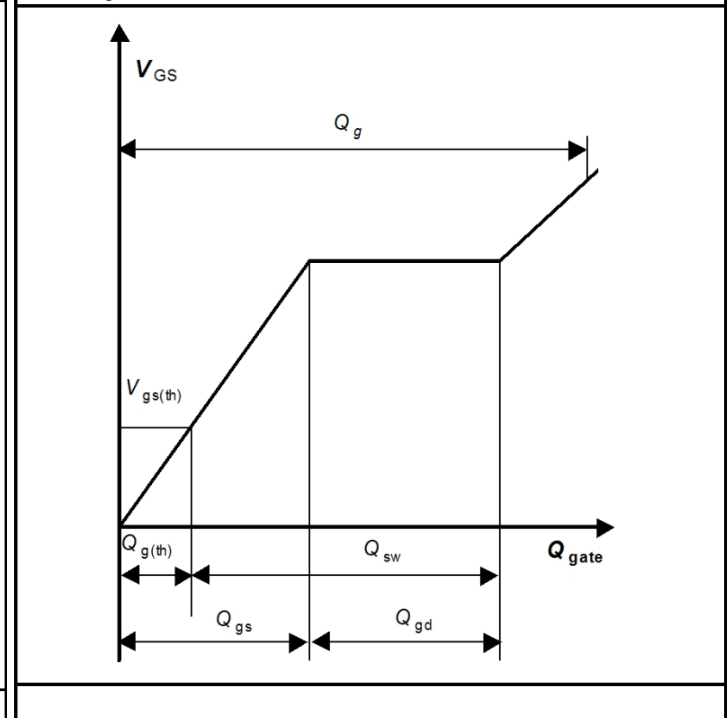
$V_{GS}=f(Q_{gate}); I_D=20 \text{ A pulsed}$ ; parameter:  $V_{DD}$

Diagram 15: Drain-source breakdown voltage



$V_{BR(DSS)}=f(T_j); I_D=1 \text{ mA}$

Gate charge waveforms



6 Package Outlines

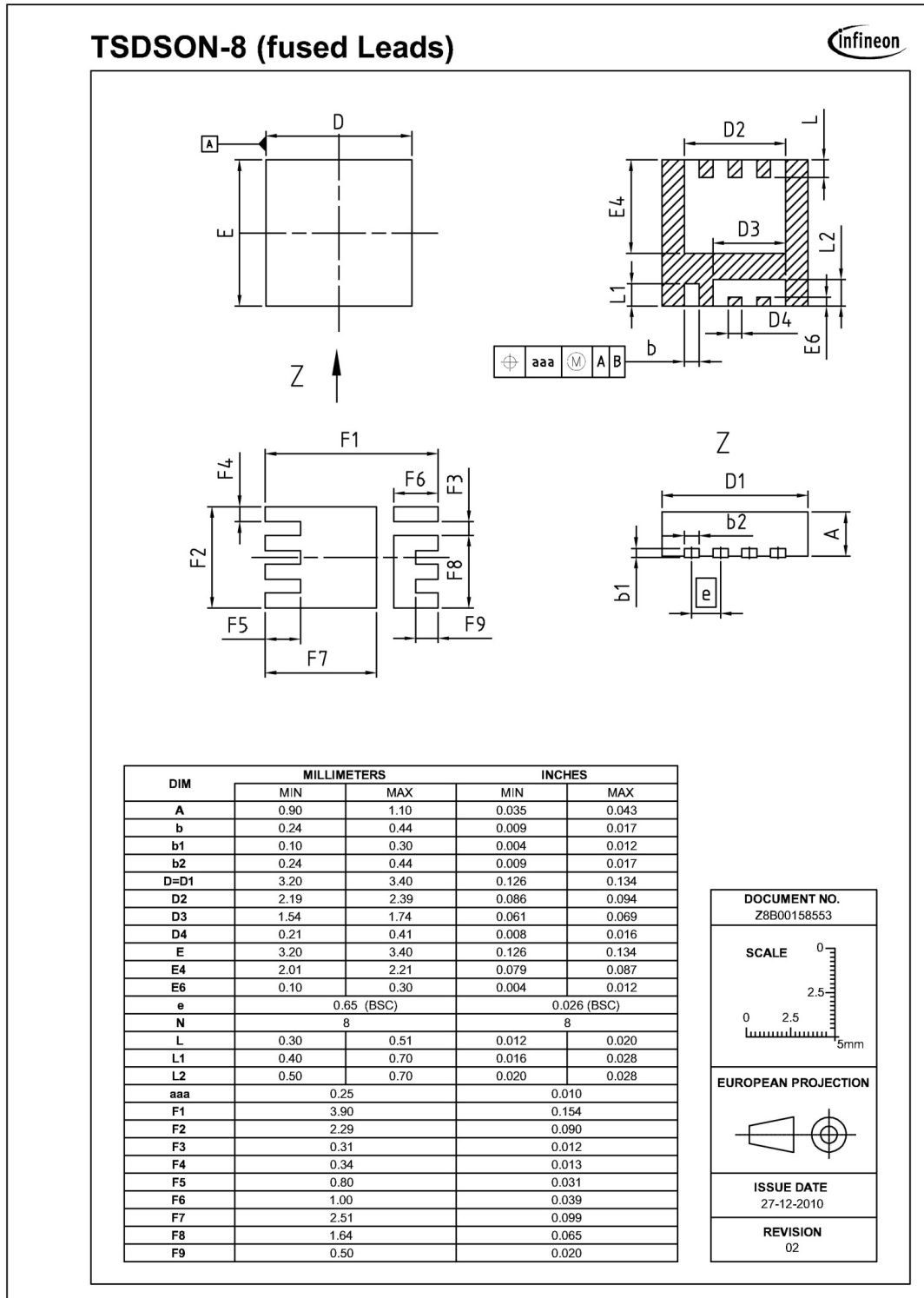


Figure 1 Outline PG-TSDSON-8 FL, dimensions in mm/inches

## Revision History

BSZ110N08NS5

**Revision: 2014-05-05, Rev. 2.1**

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.1	2014-05-05	Release of Final Version

### We Listen to Your Comments

Any information within this document that you feel is wrong, unclear or missing at all? Your feedback will help us to continuously improve the quality of this document. Please send your proposal (including a reference to this document) to:

[erratum@infineon.com](mailto:erratum@infineon.com)

### Published by

**Infineon Technologies AG**

**81726 München, Germany**

**© 2014 Infineon Technologies AG**

**All Rights Reserved.**

### Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

### Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office ([www.infineon.com](http://www.infineon.com)).

### Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

The Infineon Technologies component described in this Data Sheet may be used in life-support devices or systems and/or automotive, aviation and aerospace applications or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support, automotive, aviation and aerospace device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.